MTM23223

Silicon N-channel MOSFET

For switching

Overview

MTM23223 is N-channel MOS FET for load switch circuits.

Features

- Low voltage drive (2.5 V, 4 V)
- Realization of low on-resistance, using extremely fine process
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit			
Drain-source surrender voltage	V _{DSS}	20	V			
Gate-source surrender voltage	V _{GSS}	±10	V			
Drain current	I _D	4.5	А			
Peak drain current *1	I _{DP}	18	А			
Power dissipation *2	P _D	500	mW			
Channel temperature	T _{ch}	150	°C			
Storage temperature	T _{stg}	-55 to +150	°C			

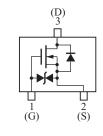
Note) *1: Pulse width $\leq 10 \ \mu s$, Duty Cycle $\leq 1\%$

*2: Measuring on ceramic substrate at 40 mm \times 38 mm \times 0.1 mm Absolute maximum rating without heat sink for $P_{\rm D}$ is 150 mW

Package

- Code
 - SMini3-G1-B
- Pin Name
- 1: Gate
- 2: Source
- 3: Drain
- Marking Symbol: BK

Internal Connection



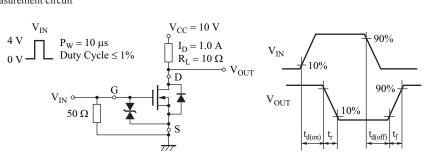
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V _{DSS}	$I_{\rm D} = 1 \text{ mA}, V_{\rm GS} = 0$	20			V
Drain-source cutoff current	I _{DSS}	$V_{\rm DS} = 20 \text{ V}, V_{\rm GS} = 0$			1.0	μΑ
Gate-source cutoff current	I _{GSS}	$V_{GS} = \pm 8 V, V_{DS} = 0$			±10	μΑ
Gate threshold voltage	V _{TH}	$I_D = 1.0 \text{ mA}, V_{DS} = 10.0 \text{ V}$	0.4	0.85	1.3	V
Drain-source ON resistance *1 R _D	D	$I_D = 1.0 \text{ A}, V_{GS} = 4.0 \text{ V}$		20	28	mΩ
	R _{DS(on)}	$I_D = 0.6 \text{ A}, V_{GS} = 2.5 \text{ V}$		26	40	
Forward transfer admittance *1	Y _{fs}	$I_D = 1.0 \text{ A}, V_{DS} = 10 \text{ V}, f = 1 \text{ kHz}$	3.5			S
Short-circuit input capacitance (Common source)	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		1 200		pF
Short-circuit output capacitance (Common source)	C _{oss}			85		pF
Reverse transfer capacitance (Common source)	C _{rss}			80		pF
Turn-on time *2	t _{on}	$V_{DD} = 10 \text{ V}, V_{GS} = 0 \text{ V to } 4 \text{ V}, I_D = 1 \text{ A}$		16		ns
Turn-off time *2	t _{off}	$V_{DD} = 10 \text{ V}, V_{GS} = 4 \text{ V to } 0 \text{ V}, I_D = 1 \text{ A}$		220		ns

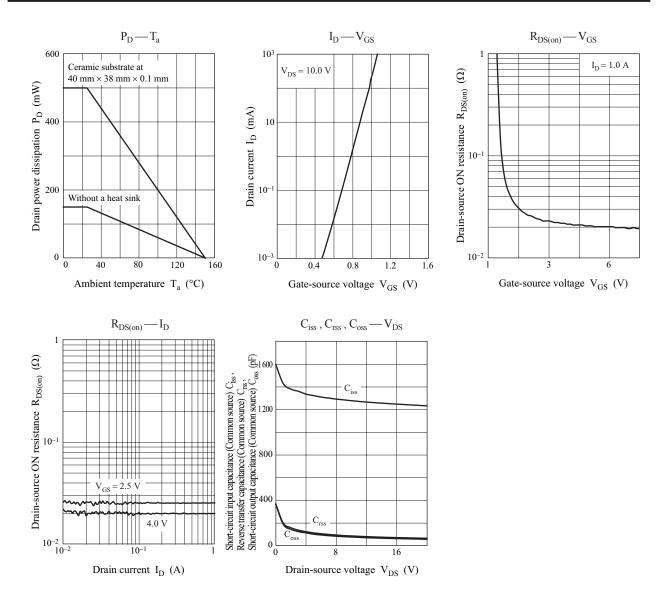
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement: Pulse width < 300 μ s, Duty Cycle < 2%

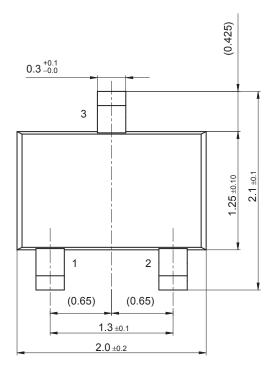
*2: t_{on} , t_{off} measurement circuit

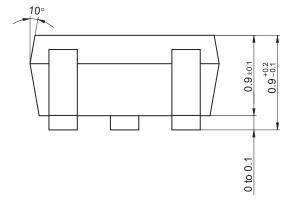


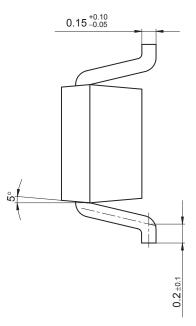


SMini3-G1-B

Unit: mm







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